

NPN SILICON HIGH FREQUENCY TRANSISTOR

UPA814TF

FEATURES

- SMALL PACKAGE OUTLINE: SOT-363 package measures just 2.0 mm x 1.25 mm
- LOW HEIGHT PROFILE: Just 0.60 mm high
- HIGH COLLECTOR CURRENT: IC MAX = 100 mA

DESCRIPTION

The UPA814TF contains two NE688 NPN high frequency silicon bipolar chips. NEC's new low profile TF package is ideal for all portable wireless applications where reducing component height is a prime consideration. Each transistor chip is independently mounted and easily configured for two stage cascade LNAs and other similar applications.

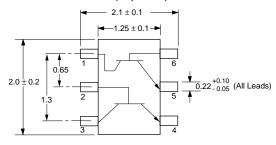
ABSOLUTE MAXIMUM RATINGS¹ (TA = 25°C)

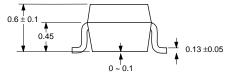
SYMBOLS	PARAMETERS	UNITS	RATINGS
Vсво	Collector to Base Voltage	V	9
VCEO	Collector to Emitter Voltage	V	6
Vево	Emitter to Base Voltage	V	2
Ic	Collector Current	mA	100
Рт	Total Power Dissipation 1 Die 2 Die	mW mW	110 200
TJ	Junction Temperature	°C	150
Tstg	Storage Temperature	°C	-65 to +150

Note: 1.Operation in excess of any one of these parameters may result in permanent damage.

OUTLINE DIMENSIONS (Units in mm)

PACKAGE OUTLINE TS06 (Top View)





PIN OUT

- 1. Collector Transistor 1
- 2. Base Transistor 2
- 3. Collector Transistor 2
- 4. Emitter Transistor 2
- Emitter Transistor 1
 Base Transistor 1

Note:

Pin 1 is the lower left most pin as the package lettering is oriented and read left to right.

ELECTRICAL CHARACTERISTICS (TA = 25°C)

PART NUMBER PACKAGE OUTLINE			UPA814TF TS06			
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX	
Ісво	Collector Cutoff Current at VcB = 5V, IE = 0	μА			0.1	
І ЕВО	Emitter Cutoff Current at VEB = 1 V, IC = 0	μА			0.1	
hFE	Forward Current Gain ¹ at VcE = 1 V, Ic = 3 mA		80	110	160	
fт	Gain Bandwidth at VcE = 3 V, Ic = 20 mA, f = 2 GHz	GHz		9.0		
Cre	Feedback Capacitance ² at VcB = 1 V, IE = 0, f = 1 MHz	pF		0.75	0.85	
S21E ²	Insertion Power Gain at VcE = 3 V, Ic =20 mA, f = 2 GHz	dB		6.5		
NF	Noise Figure at VcE = 3 V, Ic = 7 mA, f = 2 GHz	dB		1.5		
hFE1/hFE2	hfe Ratio: hfe1 = Smaller Value of Q1, or Q2 hfe2 = Larger Value of Q1 or Q2		0.85			

Notes: 1. Pulsed measurement, pulse width \leq 350 μ s, duty cycle \leq 2 %.

2. The emitter terminal should be connected to the ground terminal of the 3 terminal capacitance bridge. For Tape and Reel version use part number UPA814TF-T1, 3K per reel.

California Eastern Laboratories

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